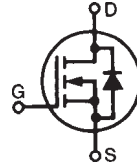


GigaMOS™ HiperFET™ Power MOSFET

IXFZ140N25T

(Electrically Isolated Tab)

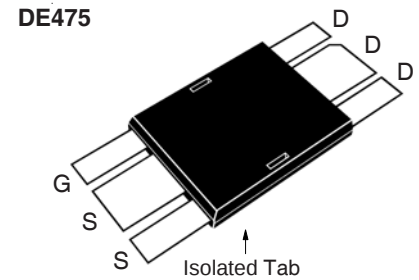
N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode



$$\begin{aligned} V_{DSS} &= 250V \\ I_{D25} &= 100A \\ R_{DS(on)} &\leq 17m\Omega \\ t_{rr} &\leq 200ns \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	250	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$	250	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ C$	100	A
I_{DM}	$T_C = 25^\circ C$, Pulse Width Limited by T_{JM}	400	A
I_A	$T_C = 25^\circ C$	40	A
E_{AS}	$T_C = 25^\circ C$	3	J
P_D	$T_C = 25^\circ C$	445	W
dv/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$	20	V/ns
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
V_{ISOL}	50/60 Hz, RMS $t = 1$ minute $I_{ISOL} \leq 1mA$ $t = 1$ second	2500 3000	V~ V~
T_L	1.6mm (0.062 in.) from Case for 10s	300	$^\circ C$
T_{SOLD}	Plastic Body for 10s	260	$^\circ C$
F_C	Mounting Force	20..120 / 4.5..27	N/lb.
Weight		3	g

Symbol	Test Conditions	Characteristic Values		
	($T_J = 25^\circ C$, Unless Otherwise Specified)	Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 3mA$	250		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4mA$	2.5		5.0 V
I_{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			± 200 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ C$			50 μA 3 mA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 60A$, Note 1			17 m Ω



G = Gate D = Drain
S = Source

Features

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
- Isolated Substrate
 - Excellent Thermal Transfer
 - Increased Temperature and Power Cycling Capability
 - High Isolation Voltage (2500V~)
- Very High Current Handling Capability
- Fast Intrinsic Diode
- Avalanche Rated

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- DC-DC Converters
- Battery Chargers
- Switch-Mode and Resonant-Mode Power Supplies
- DC Choppers
- AC Motor Drives
- Uninterruptible Power Supplies
- High Speed Power Switching Applications

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{V}$, $I_D = 60\text{A}$, Note 1	80	135	S
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		19	nF
C_{oss}			1500	pF
C_{rss}			185	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 15\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 70\text{A}$ $R_G = 1\Omega$ (External)		33	ns
t_r			29	ns
$t_{d(off)}$			92	ns
t_f			22	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 70\text{A}$		255	nC
Q_{gs}			90	nC
Q_{gd}			62	nC
R_{thJC}				0.28 $^\circ\text{C/W}$
R_{thCS}			0.15	$^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			140 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			560 A
V_{SD}	$I_F = 60\text{A}$, $V_{GS} = 0\text{V}$, Note 1			1.3 V
t_{rr}	$I_F = 70\text{A}$, $V_{GS} = 0\text{V}$ $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 75\text{V}$			200 ns
I_{RM}			9.3	A
Q_{RM}			600	nC

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

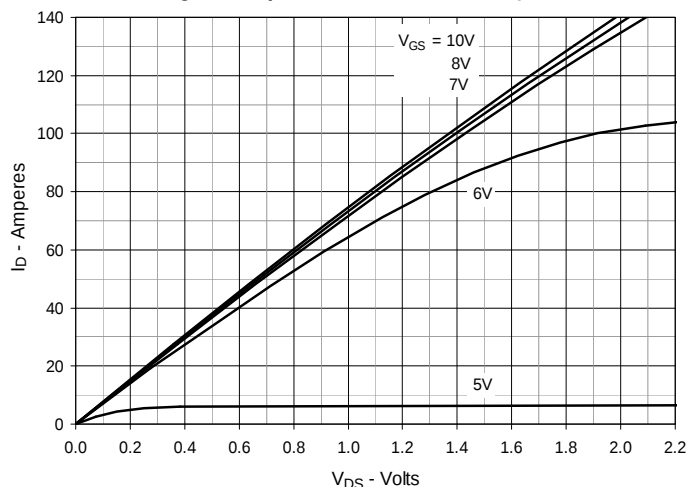


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

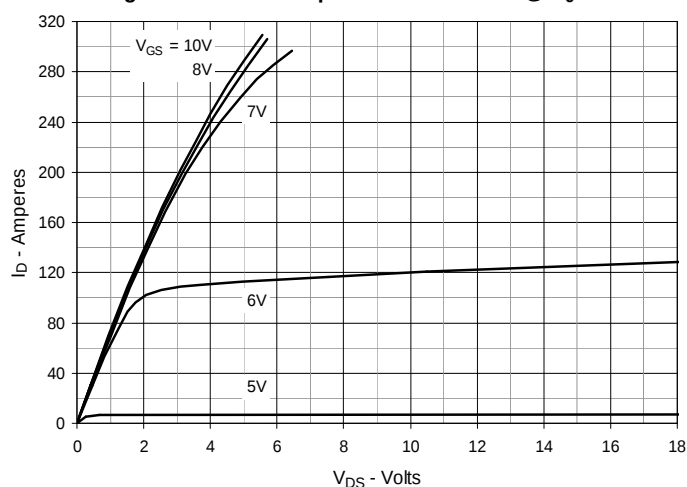


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

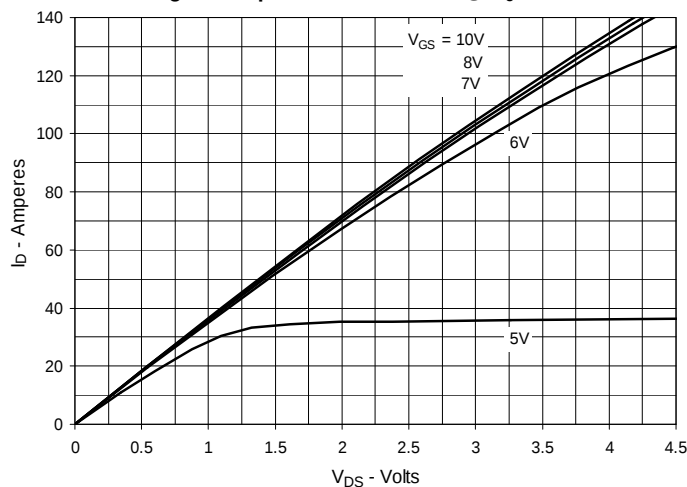


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 70\text{A}$ Value vs. Junction Temperature

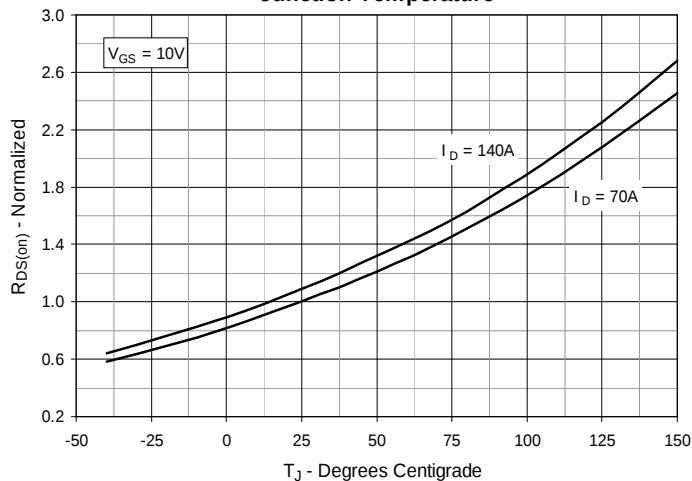


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 70\text{A}$ Value vs. Drain Current

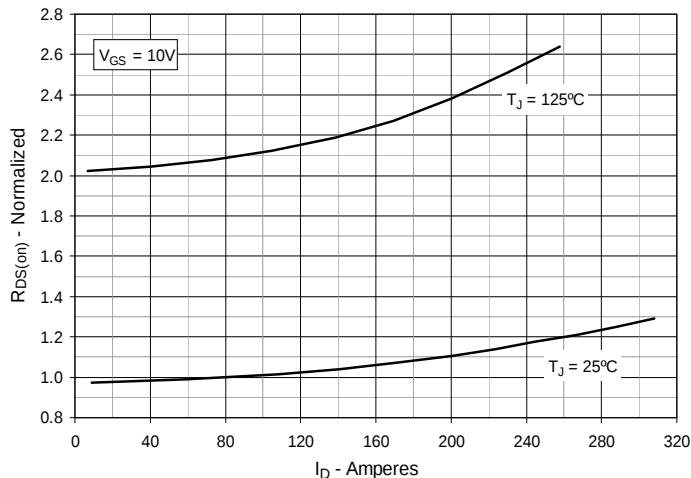


Fig. 6. Maximum Drain Current vs. Case Temperature

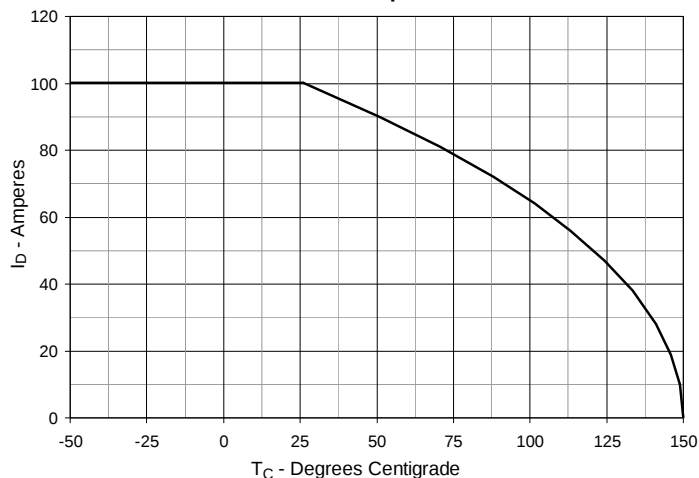


Fig. 7. Input Admittance

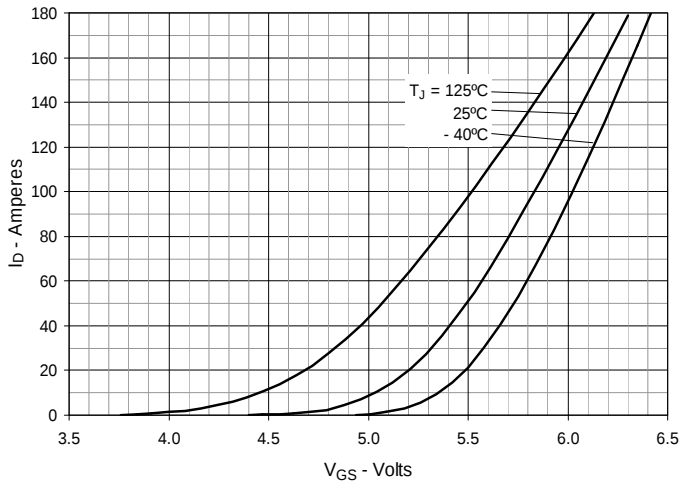


Fig. 8. Transconductance

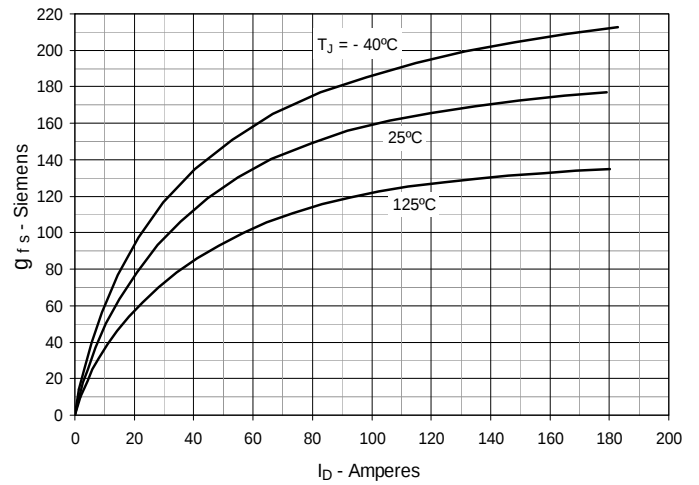


Fig. 9. Forward Voltage Drop of Intrinsic Diode

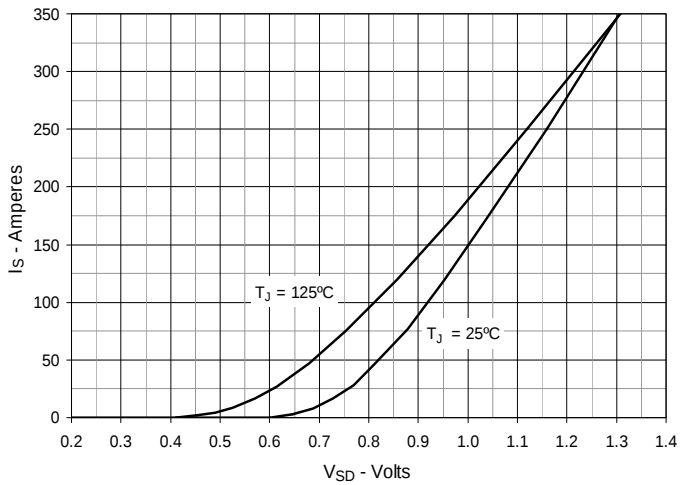


Fig. 10. Gate Charge

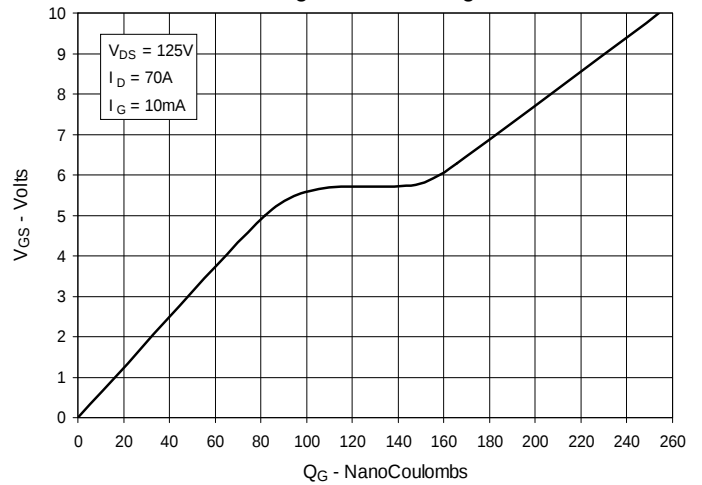


Fig. 11. Capacitance

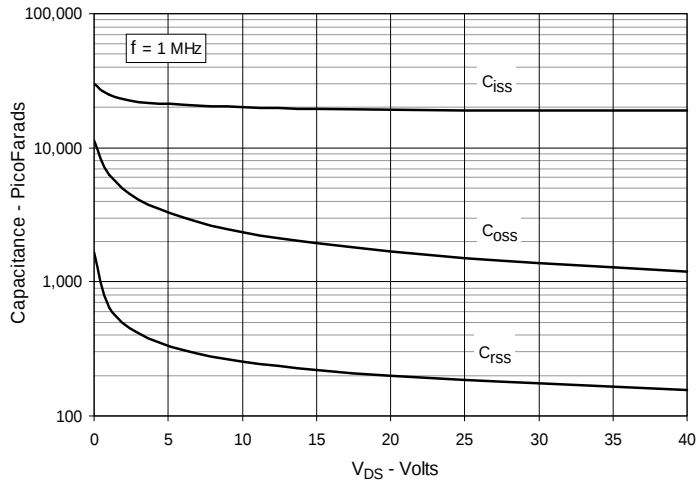


Fig. 12. Forward-Bias Safe Operating Area

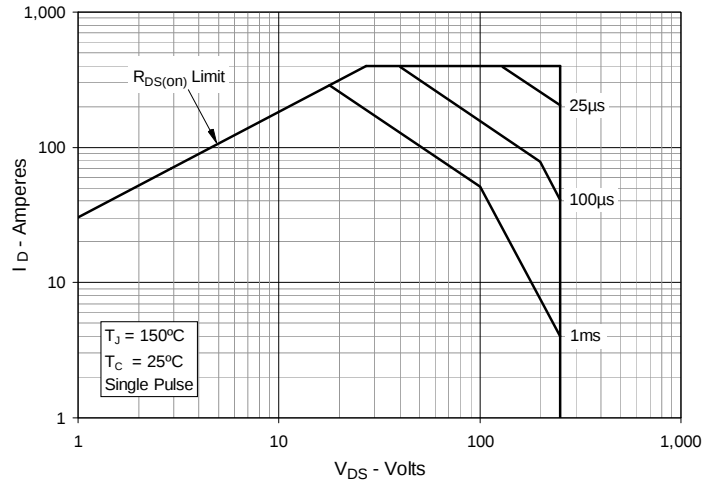
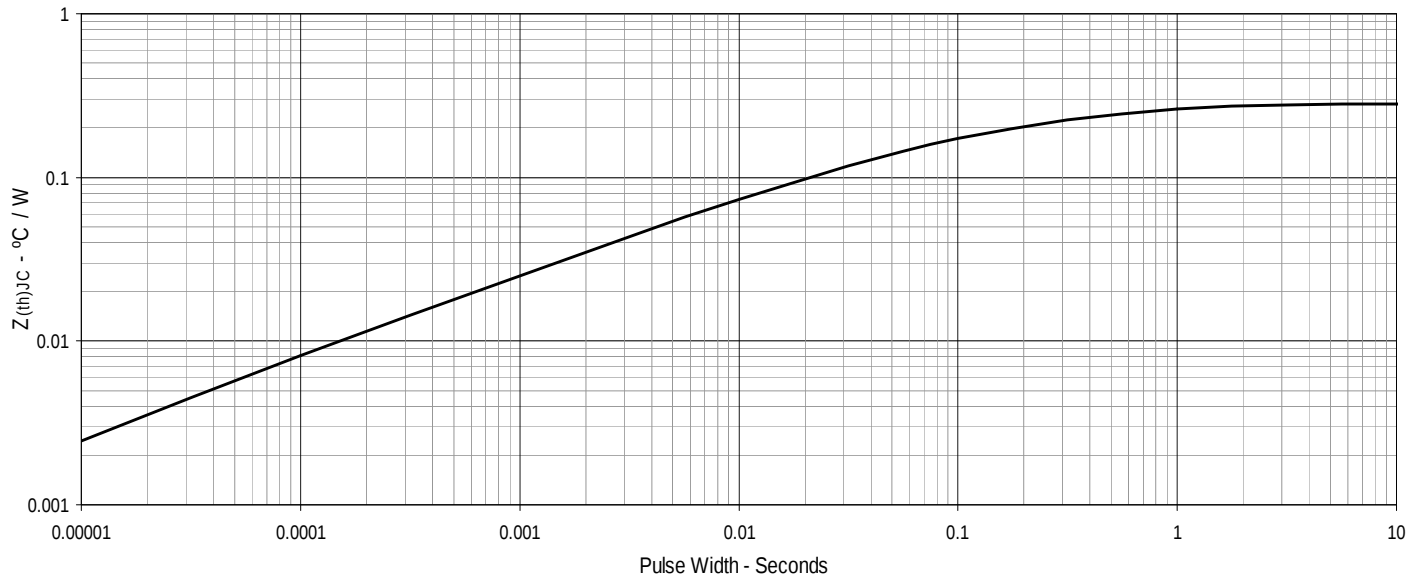


Fig. 13. Maximum Transient Thermal Impedance

DE475 (IXFZ) Outline
